polish, stain

polish, stain

100
100
100

CH,COOH
0%
so
50% HNO3
so
HCl

OH & other acids, see selectively
HF etch. 15 mins, super selective
HF etched porous silicon - amorphous silicon
HNF - HF, nitric, acetic, isopropanol, water
Clin. Silicon etching

Pt - No Pb, NaCl process
94 - Dossi, P12 E process
80, 90, thin films & sacrificial layers
easy days - water was the shortener
Bulk vis. surface in reality

Solid Bikli?
(111) plane. There are less preferential edges.

(100) plane. There are fewer defects. Every atom is in every plane.

1% 5% 10% 15% 20% 25%

(111) (100)

5% 0.2

Usechoose single crystal wafers (100)

Corner rounding issues/limitations:

5% - 400 minutes = the number of

50% - 800 minutes = the number of

Total Lateral Edge =

40% - 1200 minutes = the number of

40% - 1600 minutes = the number of

Fast v slow:

40% - 1600 minutes

Fast v slow:

<100> direction; 1 m/min

<100> direction; 3.5 m/min

<111> direction; 1 m/min

Pre A604

Si 74

14 min/m

510°C

<111> direction; 3.5 m/min

<100> direction; 1 m/min

Cassette

Red Plate

Collector

Sulfur

Tellurium

KOH 4/4/9 100 ml H2O 25°C 5 min